



IMZ2A

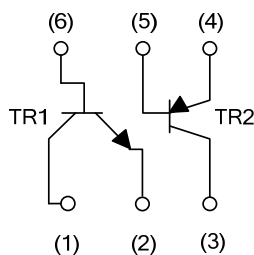
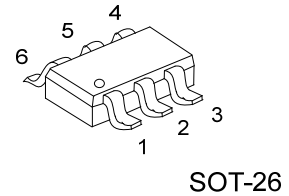
DUAL TRANSISTOR

POWER MANAGEMENT (DUAL TRANSISTOR)

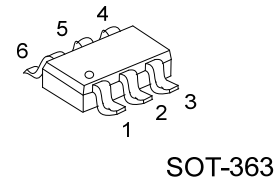
FEATURES

* Two a 9014 chip in a SMT package.

EQUIVALENT CIRCUITS



SOT-26



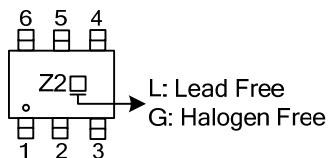
SOT-363

ORDERING INFORMATION

Ordering Number		Package	Pin Assignment						Packing
Lead Free	Halogen Free		1	2	3	4	5	6	
IMZ2AL-AG6-R	IMZ2AG-AG6-R	SOT-26	C1	E1	C2	E2	B2	B1	Tape Reel
IMZ2AL-AL6-R	IMZ2AG-AL6-R	SOT-363	C1	E1	C2	E2	B2	B1	Tape Reel

<p>IMZ2AL-AG6-R</p> <p>(1) Packing Type (2) Package Type (3) Lead Plating</p>	<p>(1) R: Tape Reel (2) AG6: SOT-26, AL6: SOT-363 (3) G: Halogen Free, L: Lead Free, Blank: Pb/Sn</p>
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MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Base Voltage	TR1	V_{CBO}	60	V
	TR2		-60	
Collector-Emitter Voltage	TR1	V_{CEO}	50	V
	TR2		-50	
Emitter-Base Voltage	TR1	V_{EBO}	7	V
	TR2		-6	
Collector Current	TR1	I_C	150	mA
	TR2		-150	
Collector Power Dissipation (Total)	SOT-26	P_c	300 (Note1)	mW
	SOT-363		200	
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55~+150	$^\circ\text{C}$

Note: 1. 200mW per element must not be exceeded.

2. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
TR1						
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C = 50\mu\text{A}$	60			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C = 1\text{mA}$	50			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E = 50\mu\text{A}$	7			V
Collector Cut-Off Current	I_{CBO}	$V_{CB} = 60\text{V}$			0.1	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB} = 7\text{V}$			0.1	μA
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_C / I_B = 50\text{mA}/5\text{mA}$			0.4	V
DC Current Transfer Ratio	h_{FE}	$V_{CE} = 6\text{V}, I_C = 1\text{mA}$	120		560	
Transition Frequency	f_T	$V_{CE} = 12\text{V}, I_E = -2\text{mA}, f = 100\text{MHz}$ (Note)		180		MHz
Output Capacitance	C_{OB}	$V_{CB} = 12\text{V}, I_E = 0\text{A}, f = 1\text{MHz}$		2	3.5	pF
TR2						
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C = -50\mu\text{A}$	-60			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C = -1\text{mA}$	-50			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E = -50\mu\text{A}$	-6			V
Collector Cut-Off Current	I_{CBO}	$V_{CB} = -60\text{V}$			-0.1	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB} = -6\text{V}$			-0.1	μA
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_C / I_B = -50\text{mA}/-5\text{mA}$			-0.5	V
DC Current Transfer Ratio	h_{FE}	$V_{CE} = -6\text{V}, I_C = -1\text{mA}$	120		560	
Transition Frequency	f_T	$V_{CE} = -12\text{V}, I_E = 2\text{mA}, f = 100\text{MHz}$ (Note)		140		MHz
Output Capacitance	C_{OB}	$V_{CB} = -12\text{V}, I_E = 0\text{A}, f = 1\text{MHz}$		4	5	pF

Note: Transition frequency of the device.

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